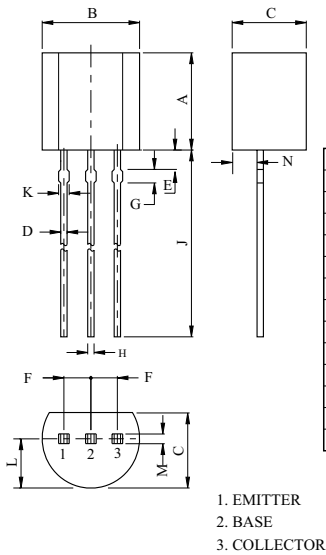
MPSA94A

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

· High Breakdown Voltage.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

TO-92

MAXIMUM RATING (Ta=25℃)

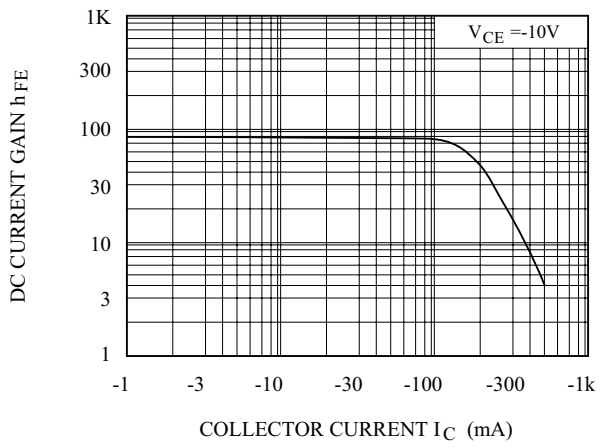
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-480	V
Collector-Emitter Voltage	V_{CEO}	-480	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-300	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

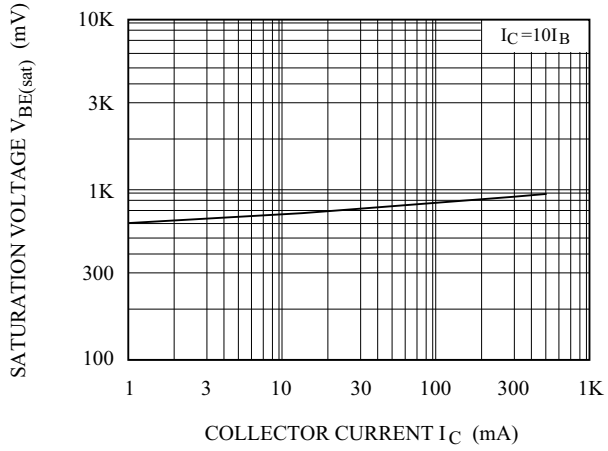
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100㎂, I_E=0	-480	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-480	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=-100㎂, I_B=0	-480	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10㎂, I_C=0	-6.0	-	-	V
Collector Cut off Current	I_{CBO}	V_{CB}=-400V, I_E=0	-	-	-100	nA
Collector Cut off Current	I_{CES}	V_{CE}=-480V, I_B=0	-	-	-1	㎂
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4V, I_C=0	-	-	-100	nA
DC Current Gain *	h_{FE}	V_{CE}=-10V, I_C=-1mA	40	-	-	
		V_{CE}=-10V, I_C=-10mA	50	-	300	
		V_{CE}=-10V, I_C=-50mA	45	-	-	
		V_{CE}=-10V, I_C=-100mA	40	-	-	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}1$	I_C=-1mA, I_B=-0.1mA	-	-	-0.35	V
	$V_{CE(sat)}2$	I_C=-20mA, I_B=-2mA	-	-	-0.5	
	$V_{CE(sat)}3$	I_C=-50mA, I_B=-5mA	-	-	-0.75	
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=-10mA, I_B=-1mA	-	-	-0.75	V

*Pulse Test : Pulse Width ≦300㎲, Duty Cycle ≦2%

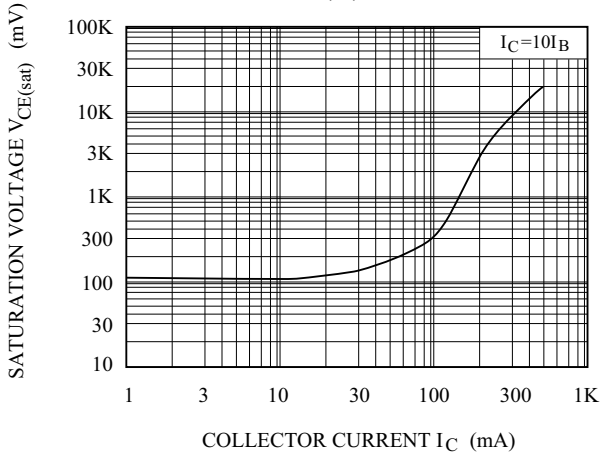
h_{FE} - I_C



$V_{BE(sat)}$ - I_C



$V_{CE(sat)}$ - I_C



C_{ob} - V_{CB}